

# Konstantin Kotlyar

## List of Publications by Year in descending order

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Version: 2024-02-01

39  
papers

118  
citations

1478505

6  
h-index

1372567

10  
g-index

39  
all docs

39  
docs citations

39  
times ranked

124  
citing authors

#	ARTICLE	IF	CITATIONS
1	Optical properties of Al <sub>x</sub> Ga <sub>1-x</sub> As nanowires with different composition in Al. AIP Conference Proceedings, 2019, , .	0.4	0
2	Influence of cryogenic dry etching on minority carriers lifetime in vertically aligned silicon nanostructures. AIP Conference Proceedings, 2019, , .	0.4	0
3	InGaN/GaN QDs nanorods for light emitters: Processing and properties. AIP Conference Proceedings, 2019, , .	0.4	1
4	Study of SiC buffer layer thickness influence on photovoltaic properties of n-GaN NWs/SiC/p-Si heterostructure. Materials Science in Semiconductor Processing, 2019, 90, 20-25.	4.0	7
5	MBE growth and Structural Properties of InAs and InGaAs Nanowires with Different Mole Fraction of In on Si and Strongly Mismatched SiC/Si(111) Substrates. Semiconductors, 2018, 52, 651-653.	0.5	2
6	The Features of GaAs Nanowire SEM Images. Semiconductors, 2018, 52, 605-608.	0.5	0
7	Low temperature plasma enhanced deposition approach for fabrication of microcrystalline GaP/Si superlattice. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2018, 36, 02D408.	2.1	7
8	Oxygen Nitrogen Mixture Effect on Aluminum Nitride Synthesis by Reactive Ion Plasma Deposition. Semiconductors, 2018, 52, 184-188.	0.5	7
9	New method for MBE growth of GaAs nanowires on silicon using colloidal Au nanoparticles. Nanotechnology, 2018, 29, 045602.	2.6	6
10	InGaN/GaN QDs Nanorods: Processing and Properties. Semiconductors, 2018, 52, 2096-2098.	0.5	0
11	Structural and Optical Properties of Wurtzite AlGaAs Nanowires Grown by MBE on Si(111) Substrate. Semiconductors, 2018, 52, 2146-2148.	0.5	3
12	Processing of GaN/Si(111) Epitaxial Structures for MEMS Applications. Semiconductors, 2018, 52, 2117-2119.	0.5	3
13	Injection microdisk lasers based on multilayers of InGaAs/GaAs quantum well-dot structures. Journal of Physics: Conference Series, 2018, 1124, 041002.	0.4	1
14	Temperature annealing effect on ITO film. Journal of Physics: Conference Series, 2018, 1124, 041035.	0.4	1
15	Effect of temperature on dry etching of III-V structures. Journal of Physics: Conference Series, 2018, 1124, 041031.	0.4	0
16	Study of p-type contact topography influence on characteristics of microdisk and microring lasers. Journal of Physics: Conference Series, 2018, 1124, 041012.	0.4	3
17	Room temperature lasing from microdisk laser in aqueous medium. Journal of Physics: Conference Series, 2018, 1124, 051007.	0.4	8
18	Solar Cell Based on Core/Shell Nanowires. Semiconductors, 2018, 52, 1568-1572.	0.5	4

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19	MBE growth of GaAs nanowires with modulated crystal structure. Journal of Physics: Conference Series, 2018, 1124, 022043.	0.4	1
20	Influence of coating layers on characteristics of microdisk lasers with InAs/InGaAs quantum dots active region. Journal of Physics: Conference Series, 2018, 1124, 041020.	0.4	0
21	MBE Growth and Structural Properties of GaP and InP Nanowires on a SiC Substrate with a Graphene Layer. Semiconductors, 2018, 52, 1428-1431.	0.5	2
22	Phosphorus-Based Nanowires Grown by Molecular-Beam Epitaxy on Silicon. Semiconductors, 2018, 52, 1416-1419.	0.5	2
23	Polymer-salt synthesis and characterization of MgO-ZnO ceramic coatings with the high transparency in UV spectral range. Optical Materials, 2018, 82, 81-87.	3.6	22
24	MBE Growth and Optical Properties of GaN, InN, and Al <sub>0.3</sub> B <sub>0.5</sub> Nanowires on SiC/Si(111) Hybrid Substrate. Advances in Condensed Matter Physics, 2018, 2018, 1-5.	1.1	0
25	MBE Growth and Optical Properties of III-V Nanowires on SiC/Si(111) Hybrid Substrate. , 2018, , .		0
26	MBE growth of ultrathin III-V nanowires on a highly mismatched SiC/Si(111) substrate. Semiconductors, 2017, 51, 1472-1476.	0.5	1
27	MBE growth and optical properties of GaN layers on SiC/Si(111) hybrid substrate. Journal of Physics: Conference Series, 2017, 917, 032014.	0.4	0
28	Influence of dry etching condition to geometry of vertically aligned silicon nanostructures. Journal of Physics: Conference Series, 2017, 917, 052030.	0.4	1
29	MBE growth of GaAs and InAs nanowires using colloidal Ag nanoparticles. Journal of Physics: Conference Series, 2017, 917, 032035.	0.4	2
30	Thermal Penetration of Gold Nanoparticles into Silicon Dioxide. Acta Physica Polonica A, 2017, 132, 366-369.	0.5	10
31	Fabrication of the structures with autocatalytic CdTe nanowires using magnetron sputtering deposition. Physics of the Solid State, 2016, 58, 2401-2405.	0.6	2
32	MBE growth and optical properties of GaN nanowires on SiC/Si(111) hybrid substrate. , 2016, , .		0
33	The use of SiC/Si(111) hybrid substrate for MBE growth of GaN nanowires. Journal of Physics: Conference Series, 2016, 741, 012027.	0.4	3
34	InGaN/GaN heterostructures with lateral confinement for light emitting diodes. Journal of Physics: Conference Series, 2016, 741, 012083.	0.4	1
35	Features of AlN film grown by ion-plasma sputtering. Journal of Physics: Conference Series, 2016, 741, 012041.	0.4	0
36	Growth and optical properties of filamentary GaN nanocrystals grown on a hybrid SiC/Si(111) substrate by molecular beam epitaxy. Physics of the Solid State, 2016, 58, 1952-1955.	0.6	10

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37	Optical field distribution in quasy-ID nanostructures. Journal of Physics: Conference Series, 2016, 741, 012154.	0.4	1
38	MBE growth and optical properties of GaN nanowires on SiC/Si(111) hybrid substrate. AIP Conference Proceedings, 2016, , .	0.4	6
39	Development of methods for orderly growth of nanowires. Journal of Physics: Conference Series, 2015, 661, 012053.	0.4	1